

MICRO ELECTRONICS

BC351

**PNP
SILICON
TRANSISTOR**

DESCRIPTION

BC351 is PNP silicon planar transistor designed for AF small signal amplifier stages.

TO-92A



EBC

ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage	V _{CEO}	30V
Collector-Base Voltage	V _{CB0}	40V
Emitter-Base Voltage	V _{EB0}	5V
Collector Current	I _C	100mA
Continuous Power Dissipation	P _d	300mW
Operating & Storage Junction Temperature	T _j , T _{stg}	-55 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS	
Collector-Emitter Breakdown Voltage	LV _{CEO}	30		V	I _C = 1mA	I _B = 0
Collector-Base Breakdown Voltage	BV _{CB0}	40		V	I _C = 100µA	I _E = 0
Emtter-Base Breakdown Voltage	BV _{EB0}	5		V	I _E = 100µA	I _C = 0
Collector Cutoff Current	I _{CBO}		100	nA	V _{CB} = 20V	I _E = 0
D.C. Current Gain	HFE	40	450		I _C = 2mA	V _{CE} = 5V
		40	120		I _C = 2mA	V _{CE} = 5V
		110	220		I _C = 2mA	V _{CE} = 5V
		200	450		I _C = 2mA	V _{CE} = 5V
Collector-Emitter Saturation Voltage	V _{CE(sat)}		0.25	V	I _C = 10mA	I _B = 1mA
Output Capacitance	C _{ob}		4	pF	V _{CB} = 10V	f = 1MHz
Current Gain Bandwidth Product	f _T	125		MHz	I _C = 5mA	V _{CE} = 10V f = 100MHz

* Pulse test : pulse width < 300µS, duty cycle < 2%.



MICRO ELECTRONICS LTD.

38, Hung To Road, Microtron Building, Kwun Tong, Kowloon, Hong Kong.
Kwun Tong P.O. Box 69477 Hong Kong. Fax No. 2341 0321 Telex: 43510 Micro Hx. Tel: 2343 0181-5

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